

IRF7836PbF

HEXFET® Power MOSFET

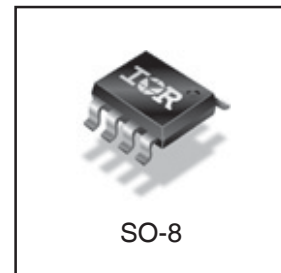
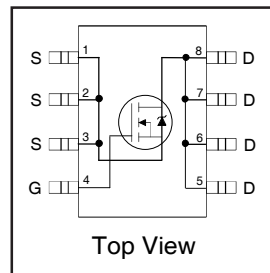
Applications

- Synchronous MOSFET for Notebook Processor Power
- Synchronous Rectifier MOSFET for isolated DC-DC Converters in Networking Systems

V_{DSS}	R_{DS(on)} max	Qg
30V	5.7mΩ @ V_{GS} = 10V	18nC

Benefits

- Very Low R_{DS(on)} at 4.5V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- 100% Tested for R_G
- Lead-Free



Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	30	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	17	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	13	
I _{DM}	Pulsed Drain Current ①	130	
P _D @ T _A = 25°C	Power Dissipation ④	2.5	W
P _D @ T _A = 70°C	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/°C
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJL}	Junction-to-Drain Lead ⑤	—	20	°C/W
R _{θJA}	Junction-to-Ambient ④⑤	—	50	

Notes ① through ⑤ are on page 9

www.irf.com

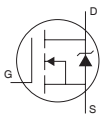
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.024	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	4.5	5.7	mΩ	V _{GS} = 10V, I _D = 17A ③
		—	5.7	7.1		V _{GS} = 4.5V, I _D = 13A ③
V _{GS(th)}	Gate Threshold Voltage	1.35	1.8	2.35	V	V _{DS} = V _{GS} , I _D = 50μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	-6.2	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	150		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
gfs	Forward Transconductance	70	—	—	S	V _{DS} = 15V, I _D = 13A
Q _g	Total Gate Charge	—	18	27	nC	V _{DS} = 15V V _{GS} = 4.5V I _D = 13A See Fig. 17 & 18
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	4.1	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.5	—		
Q _{gd}	Gate-to-Drain Charge	—	5.8	—		
Q _{godr}	Gate Charge Overdrive	—	6.6	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	7.3	—		
Q _{oss}	Output Charge	—	11	—	nC	V _{DS} = 16V, V _{GS} = 0V
R _g	Gate Resistance	—	1.0	1.7	Ω	
t _{d(on)}	Turn-On Delay Time	—	8.9	—	ns	V _{DD} = 15V, V _{GS} = 4.5V I _D = 13A Clamped Inductive Load See Fig. 15
t _r	Rise Time	—	11	—		
t _{d(off)}	Turn-Off Delay Time	—	12	—		
t _f	Fall Time	—	4.2	—		
C _{iss}	Input Capacitance	—	2400	—	pF	V _{GS} = 0V V _{DS} = 15V f = 1.0MHz
C _{oss}	Output Capacitance	—	500	—		
C _{rss}	Reverse Transfer Capacitance	—	230	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	130	mJ
I _{AR}	Avalanche Current ①	—	13	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	130	A	
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 13A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	15	23	ns	T _J = 25°C, I _F = 13A, V _{DD} = 15V
Q _{rr}	Reverse Recovery Charge	—	17	26	nC	di/dt = 500A/μs ③ See Fig. 16
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

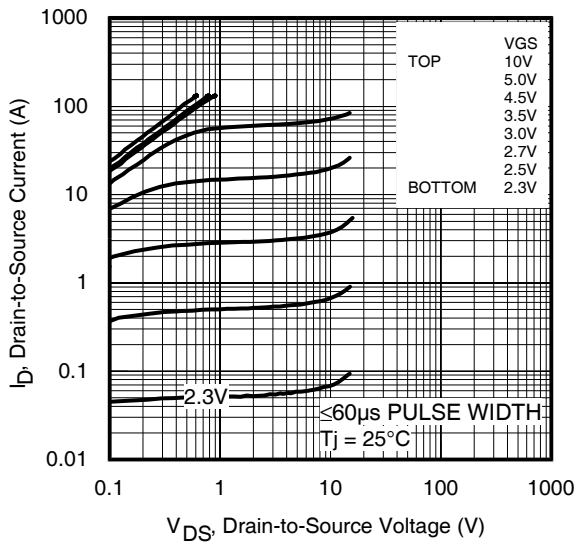


Fig 1. Typical Output Characteristics

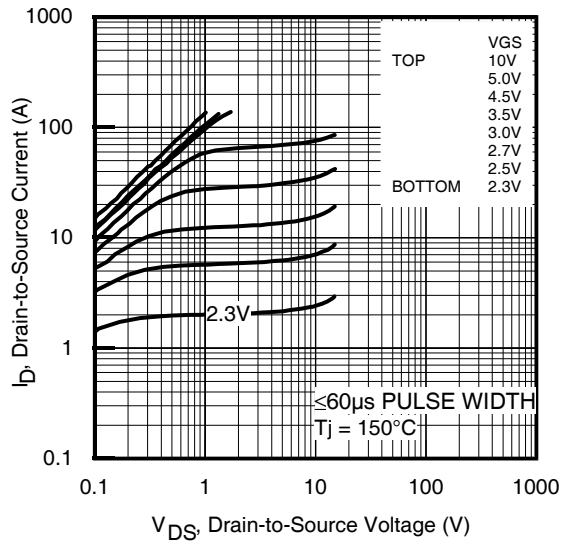


Fig 2. Typical Output Characteristics

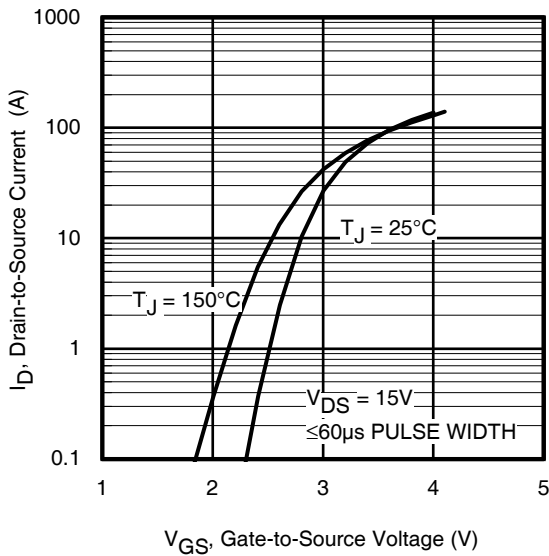


Fig 3. Typical Transfer Characteristics

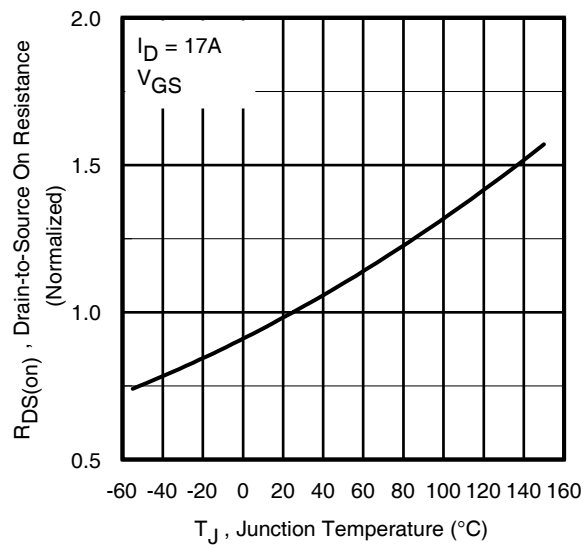


Fig 4. Normalized On-Resistance vs. Temperature

IRF7836PbF

International
IR Rectifier

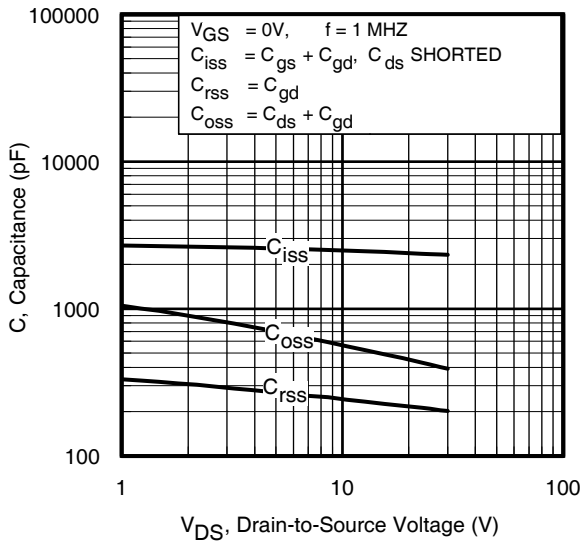


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

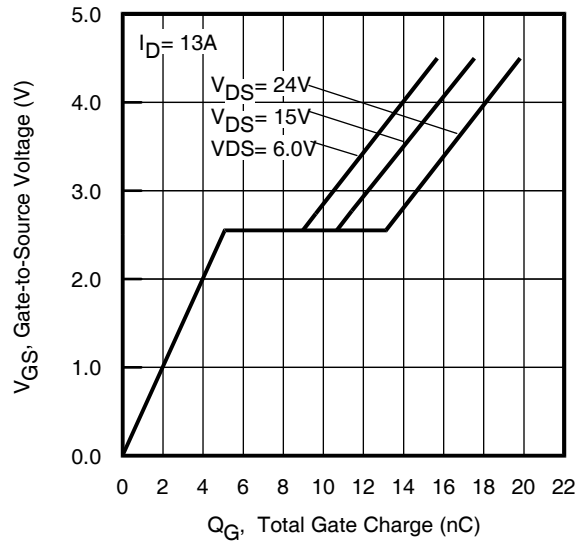


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

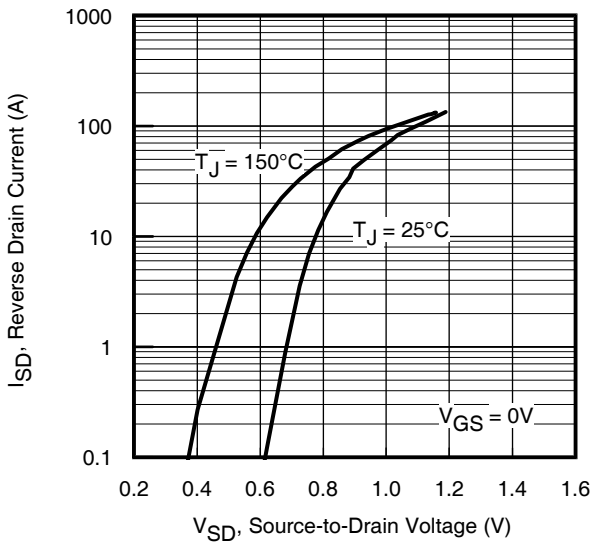


Fig 7. Typical Source-Drain Diode Forward Voltage

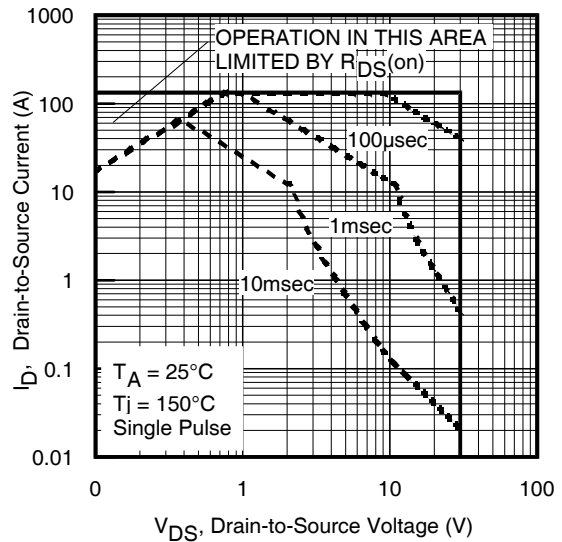


Fig 8. Maximum Safe Operating Area

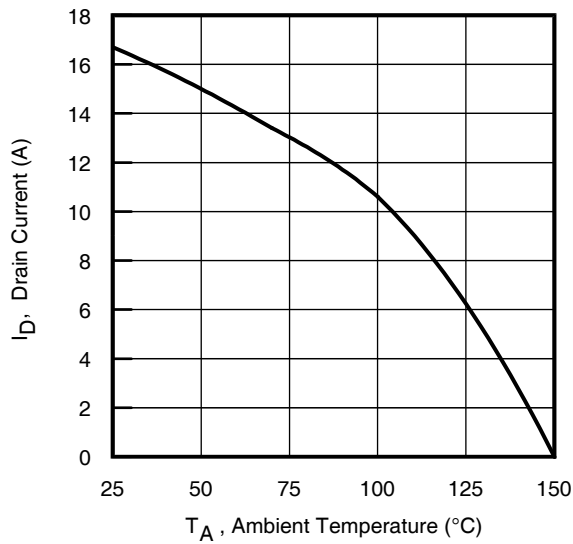


Fig 9. Maximum Drain Current vs. Case Temperature

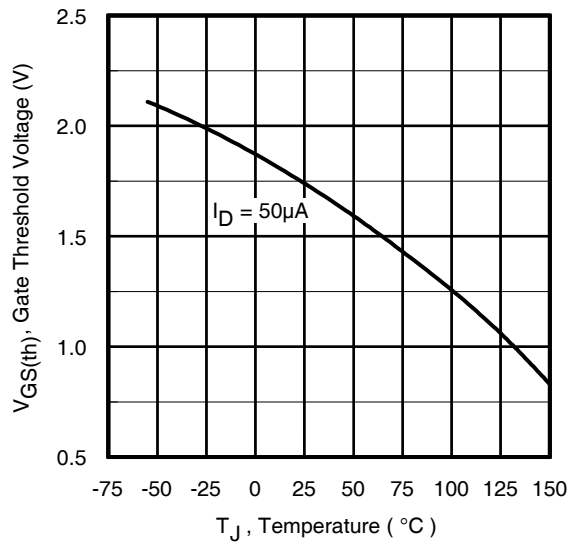


Fig 10. Threshold Voltage vs. Temperature

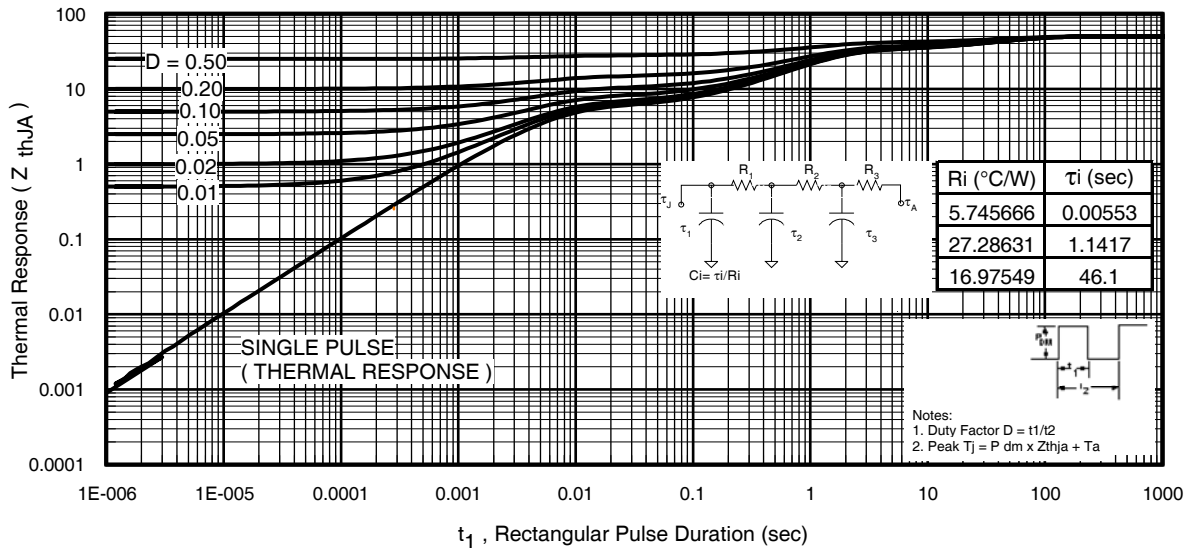


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRF7836PbF

International
IR Rectifier

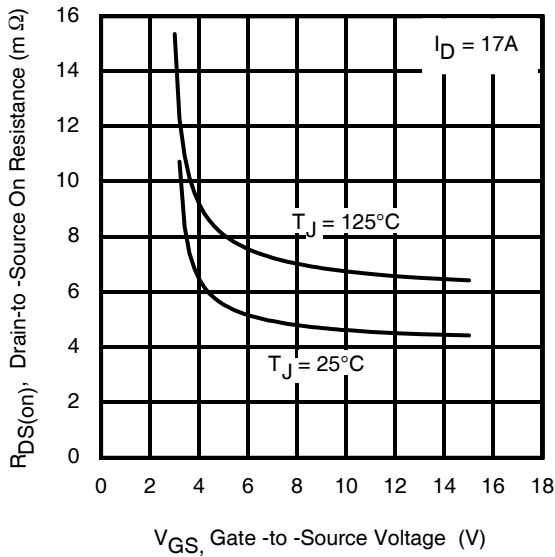


Fig 12. On-Resistance vs. Gate Voltage

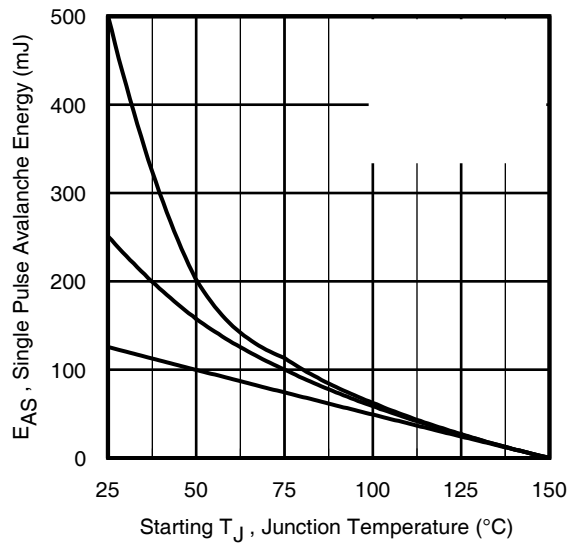


Fig 13. Maximum Avalanche Energy vs. Drain Current

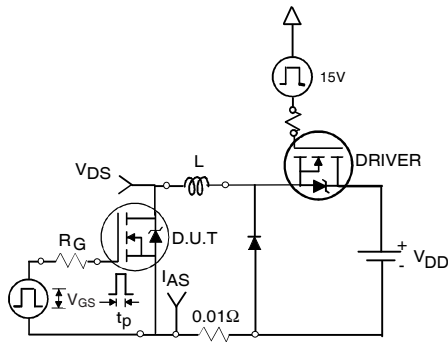


Fig 14a. Unclamped Inductive Test Circuit

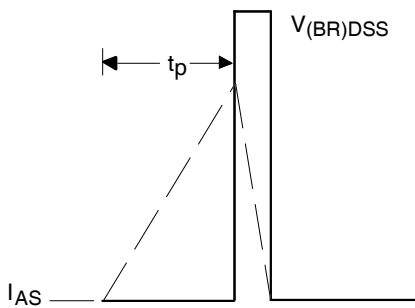


Fig 14b. Unclamped Inductive Waveforms

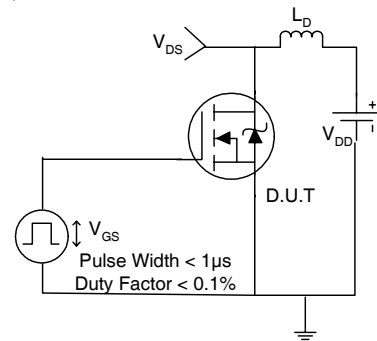


Fig 15a. Switching Time Test Circuit

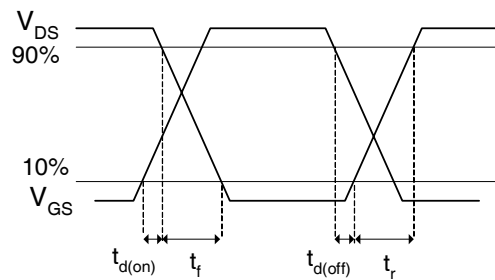
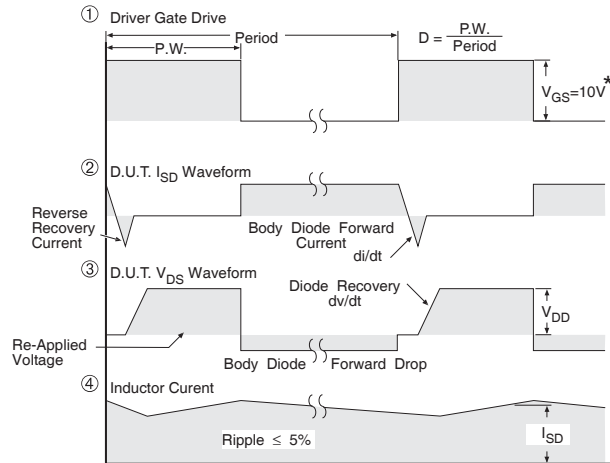
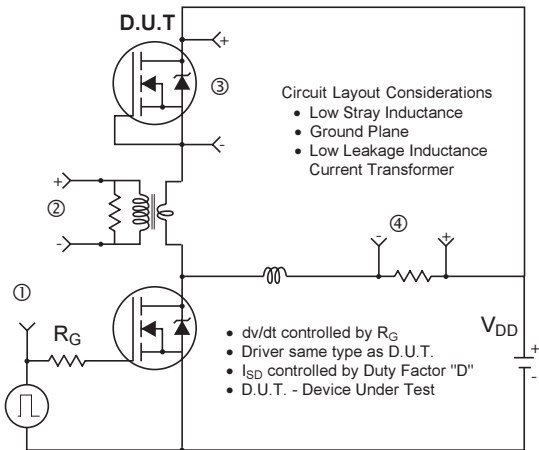


Fig 15b. Switching Time Waveforms



* $V_{GS} = 5V$ for Logic Level Devices

Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

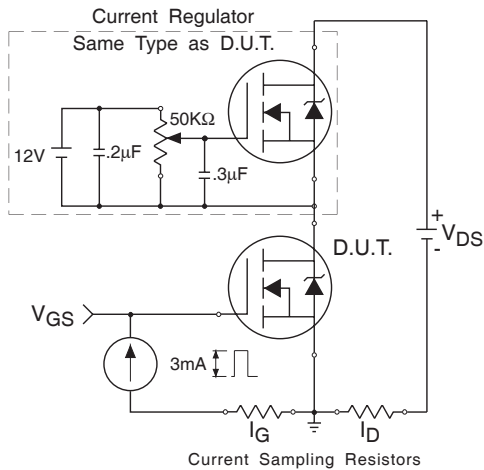


Fig 17. Gate Charge Test Circuit

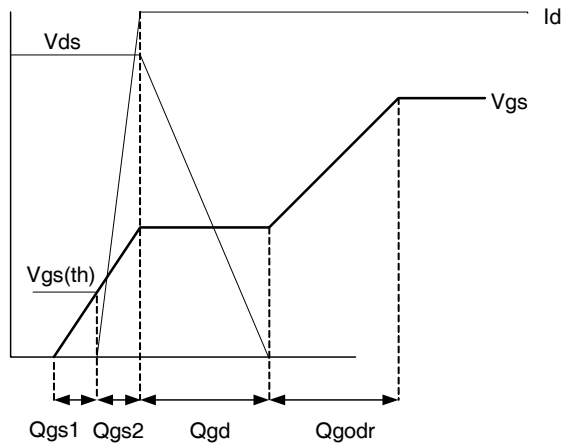
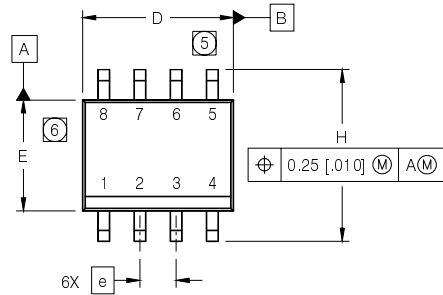


Fig 18. Gate Charge Waveform

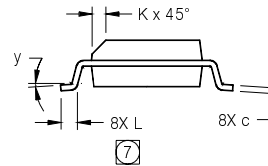
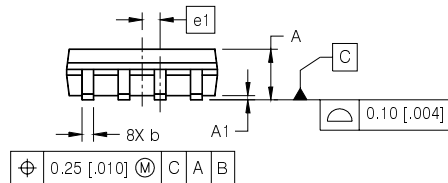
IRF7836PbF

International
IR Rectifier

SO-8 Package Outline (Dimensions are shown in millimeters (inches))



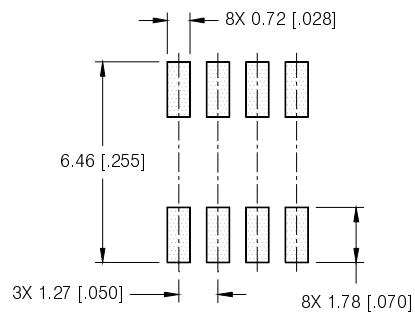
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0"	8"	0"	8"



NOTES:

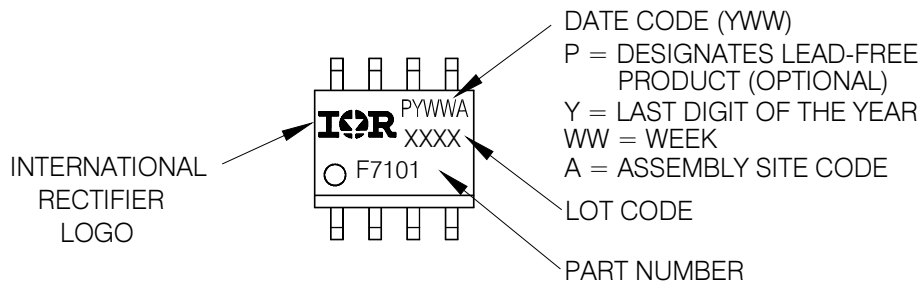
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT

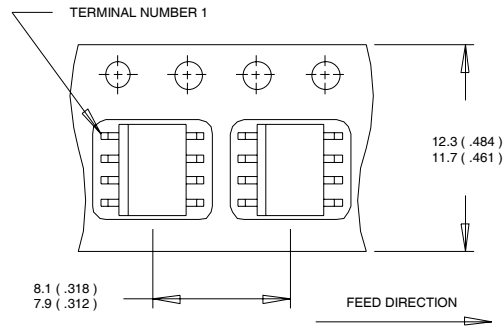


SO-8 Part Marking

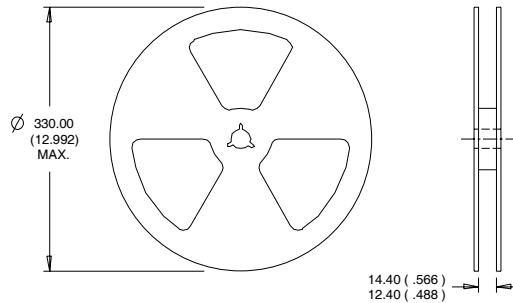
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.4\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 13\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.
- ⑤ R_θ is measured at T_J approximately 90°C .

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualification Standards can be found on IR's Web site.